

# XP151A11B0MR

ETR1117\_001

## Power MOSFET

### ■ GENERAL DESCRIPTION

The XP151A11B0MR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

In order to counter static, a gate protect diode is built-in.

The small SOT-23 package makes high density mounting possible.

### ■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

### ■ FEATURES

**Low On-State Resistance** :  $R_{ds(on)} = 0.12\Omega @ V_{gs} = 10V$   
:  $R_{ds(on)} = 0.17\Omega @ V_{gs} = 4.5V$

**Ultra High-Speed Switching**

**Gate Protect Diode Built-in**

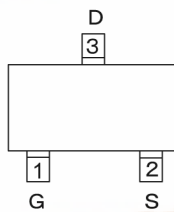
**Driving Voltage** : 4.5V

**N-Channel Power MOSFET**

**DMOS Structure**

**Small Packabe** : SOT-23

### ■ PIN CONFIGURATION

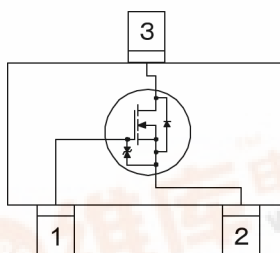


SOT-23  
(TOP VIEW)

### ■ PIN ASSIGNMENT

PIN NUMBER	PIN NAME	FUNCTION
1	G	Gate
2	S	Source
3	D	Drain

### ■ EQUIVALENT CIRCUIT



N-channel MOSFET  
(1 device built-in)

### ■ ABSOLUTE MAXIMUM RATINGS

$T_a = 25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain - Source Voltage	$V_{ds}$	30	V
Gate - Source Voltage	$V_{gs}$	$\pm 20$	V
Drain Current (DC)	$I_d$	1	A
Drain Current (Pulse)	$I_{dp}$	4	A
Reverse Drain Current	$I_{dr}$	1	A
Channel Power Dissipation *	$P_d$	0.5	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$

\* When implemented on a ceramic PCB

# XP151A11B0MR

## ELECTRICAL CHARACTERISTICS

### DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds= 30V, Vgs= 0V	-	-	10	$\mu$ A
Gate-Source Leak Current	Igss	Vgs= $\pm$ 20V, Vds= 0V	-	-	$\pm$ 10	$\mu$ A
Gate-Source Cut-Off Voltage	Vgs(off)	Id= 1mA, Vds= 10V	1.0	-	3.0	V
Drain-Source On-State Resistance *1	Rds(on)	Id= 0.5A, Vgs= 10V	-	0.09	0.12	$\Omega$
		Id= 0.5A, Vgs= 4.5V	-	0.13	0.17	$\Omega$
Forward Transfer Admittance *1	Yfs	Id= 0.5A, Vds= 10V	-	2.4	-	S
Body Drain Diode Forward Voltage	Vf	If= 1A, Vgs= 0V	-	0.8	1.1	V

\*1 Effective during pulse test.

### Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds= 10V, Vgs=0V f=1MHz	-	150	-	pF
Output Capacitance	Coss		-	90	-	pF
Feedback Capacitance	Crss		-	30	-	pF

### Switching Characteristics

Ta = 25°C

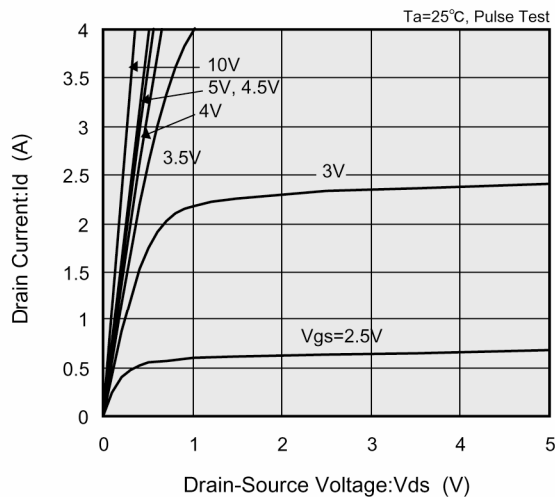
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= 5V, Id= 0.5A Vdd= 10V	-	10	-	ns
Rise Time	tr		-	15	-	ns
Turn-Off Delay Time	td (off)		-	25	-	ns
Fall Time	tf		-	45	-	ns

### Thermal Characteristics

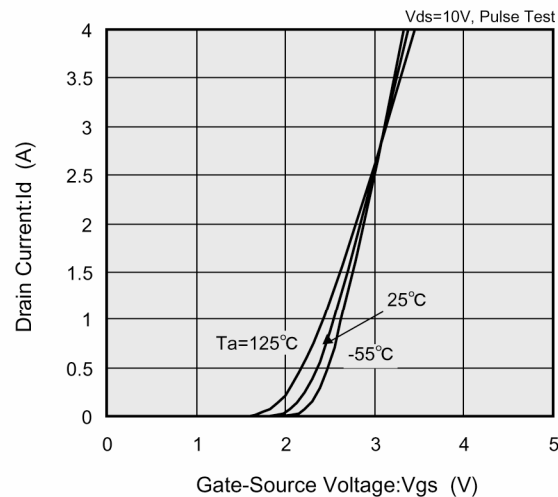
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	250	-	°C/W

# ■ TYPICAL PERFORMANCE CHARACTERISTICS

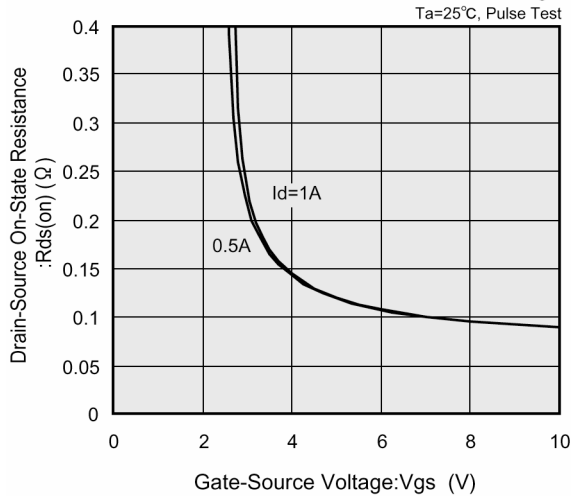
(1) Drain Current vs. Drain-Source Voltage



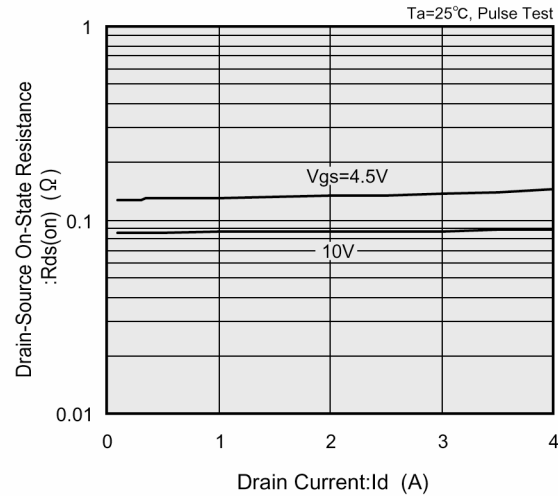
(2) Drain Current vs. Gate-Source Voltage



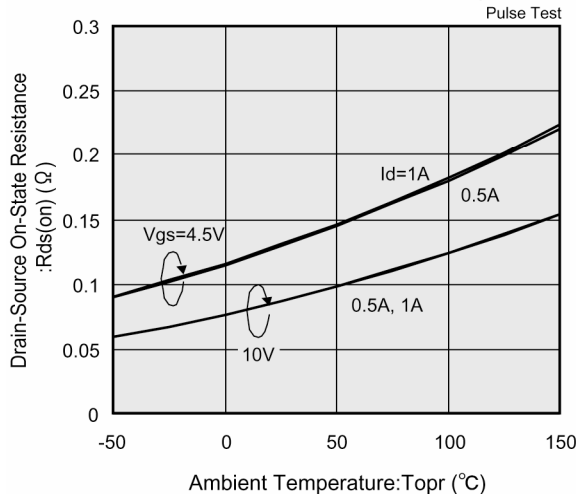
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



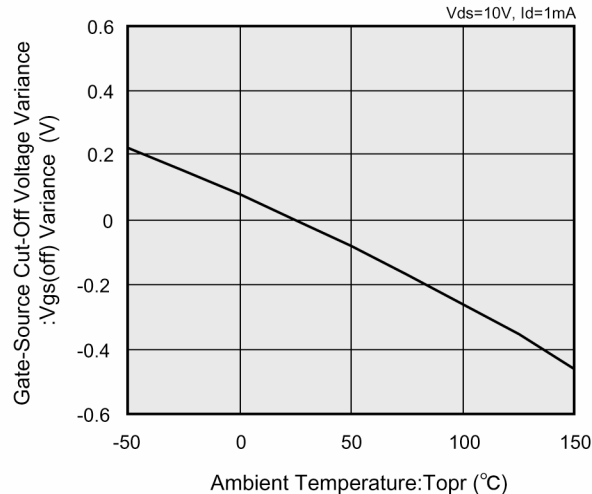
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature



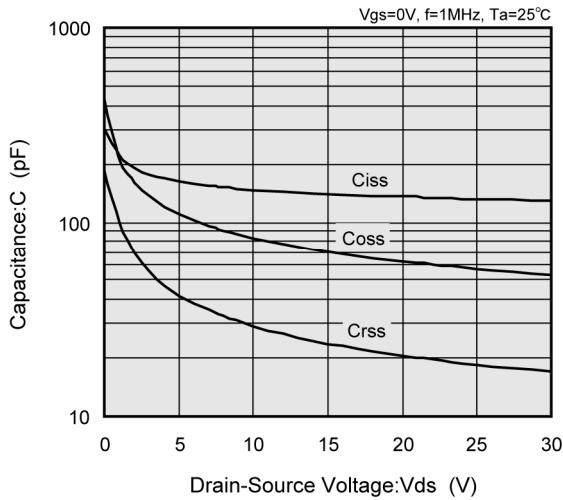
(6) Gate Source Cut-Off Voltage Variance vs. Ambient Temperature



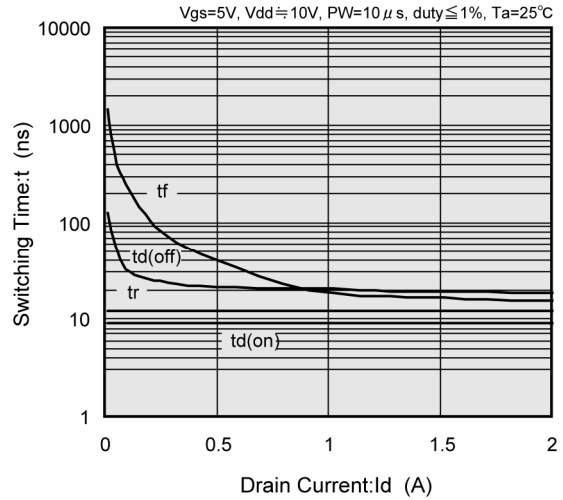
# XP151A11B0MR

## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

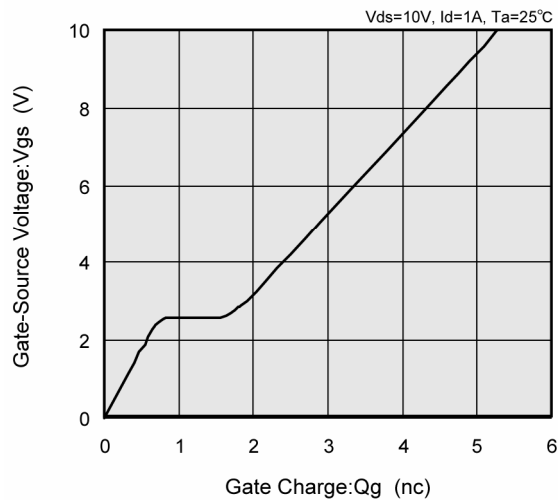
(7) Capacitance vs. Drain-Source Voltage



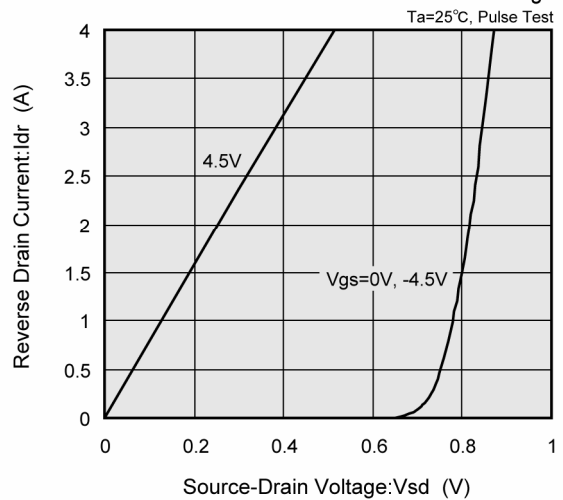
(8) Switching Time vs. Drain Current



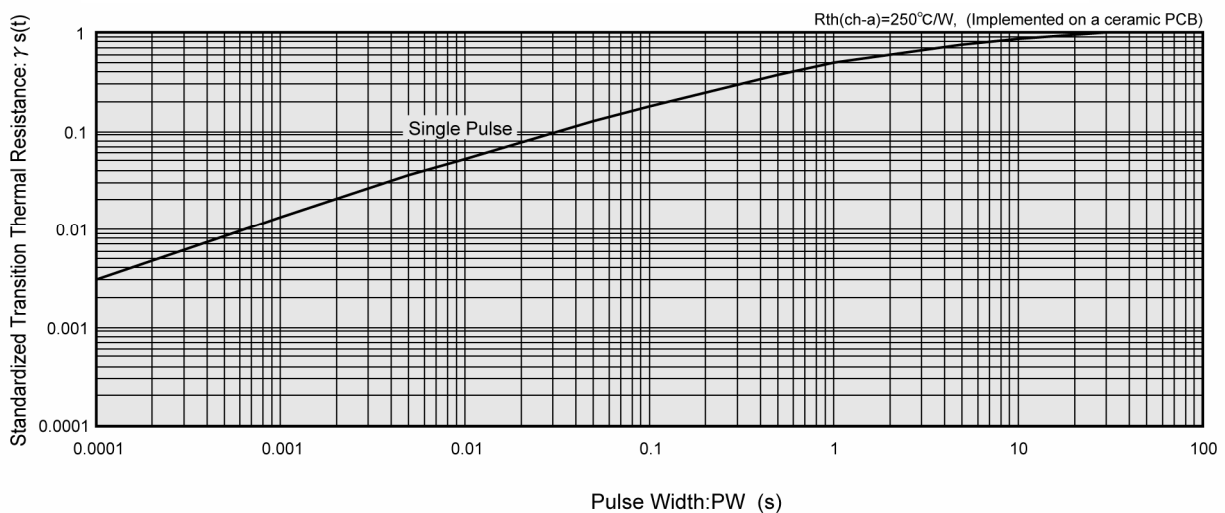
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



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